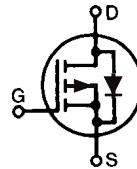


PolarP™
Power MOSFET

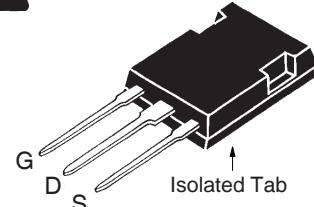
IXTR20P50P

P-Channel Enhancement Mode
Avalanche Rated



V_{DSS} = - 500V
I_{D25} = - 13A
R_{DS(on)} ≤ 490mΩ

ISOPLUS247
E153432



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	T _J = 25°C to 150°C	- 500	V	
V_{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	- 500	V	
V_{GSS}	Continuous	±20	V	
V_{GSM}	Transient	±30	V	
I_{D25}	T _C = 25°C	-13	A	
I_{DM}	T _C = 25°C, Pulse Width Limited by T _{JM}	- 60	A	
I_A	T _C = 25°C	- 20	A	
E_{AS}	T _C = 25°C	2.5	J	
dv/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	10	V/ns	
P_D	T _C = 25°C	190	W	
T_J		-55 ... +150	°C	
T_{JM}		150	°C	
T_{stg}		-55 ... +150	°C	
T_L	Maximum Lead Temperature for Soldering	300	°C	
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C	
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~	
F_c	Mounting Force	20..120/4.5..27	N/lb	
Weight		5	g	

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	V _{GS} = 0V, I _D = - 250μA	- 500		V
V_{GS(th)}	V _{DS} = V _{GS} , I _D = - 250μA	- 2.0		- 4.5 V
I_{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100 nA
I_{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 125°C			- 25 μA - 200 μA
R_{DS(on)}	V _{GS} = -10V, I _D = -10A, Note 1			490 mΩ

Features

- Silicon chip on Direct-Copper Bond (DCB) Substrate
 - UL Recognized Package
 - Isolated Mounting Surface
 - 2500V~ Electrical Isolation
- Avalanche Rated
- Fast Intrinsic Diode
- The Rugged PolarP™ Process
- Low Q_G
- Low Drain-to-Tab Capacitance
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

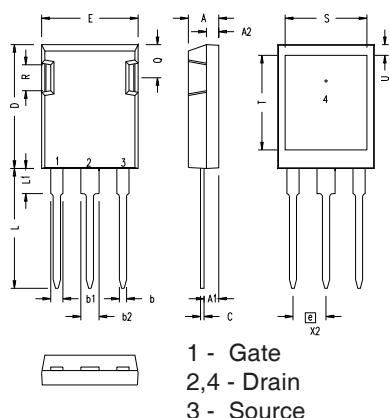
- High-Side Switches
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g _{fs}	V _{DS} = -10V, I _D = -10A, Note 1	11	18	S
C _{iss}	V _{GS} = 0V, V _{DS} = -25V, f = 1MHz	5120	pF	
C _{oss}		525	pF	
C _{rss}		75	pF	
t _{d(on)}	Resistive Switching Times V _{GS} = -10V, V _{DS} = 0.5 • V _{DSS} , I _D = -10A R _G = 3Ω (External)	26	ns	
t _r		32	ns	
t _{d(off)}		80	ns	
t _f		34	ns	
Q _{g(on)}	V _{GS} = -10V, V _{DS} = 0.5 • V _{DSS} , I _D = -10A	103	nC	
Q _{gs}		28	nC	
Q _{gd}		38	nC	
R _{thJC}			0.66 °C/W	
R _{thCS}		0.15	°C/W	

Source-Drain Diode

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I _s	V _{GS} = 0V			- 20 A
I _{SM}	Repetitive, Pulse Width Limited by T _{JM}			- 80 A
V _{SD}	I _F = -10A, V _{GS} = 0V, Note 1			- 2.8 V
t _{rr}	I _F = -10A, -di/dt = -150A/μs V _R = -100V, V _{GS} = 0V	406	ns	
Q _{RM}		8.93	μC	
I _{RM}		- 44	A	

Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

ISOPLUS247 (IXTR) Outline

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

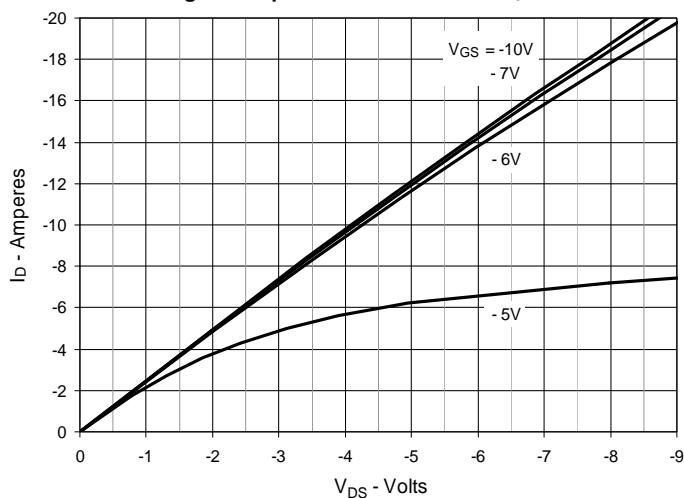
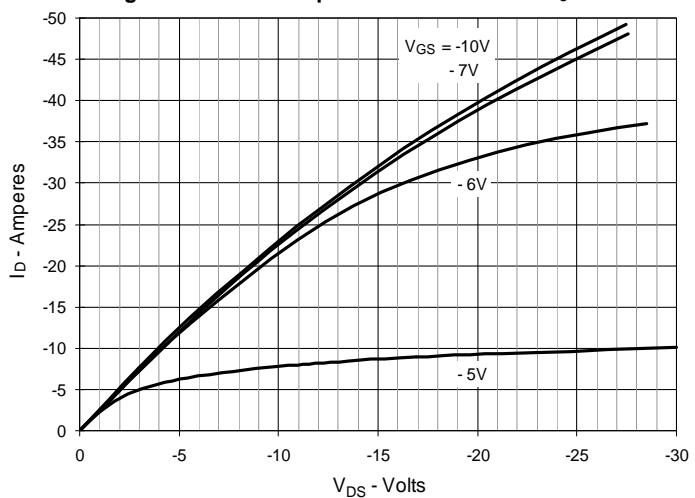
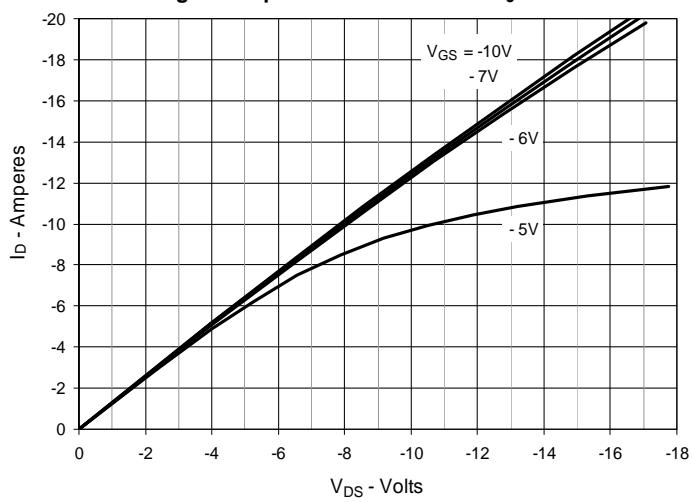
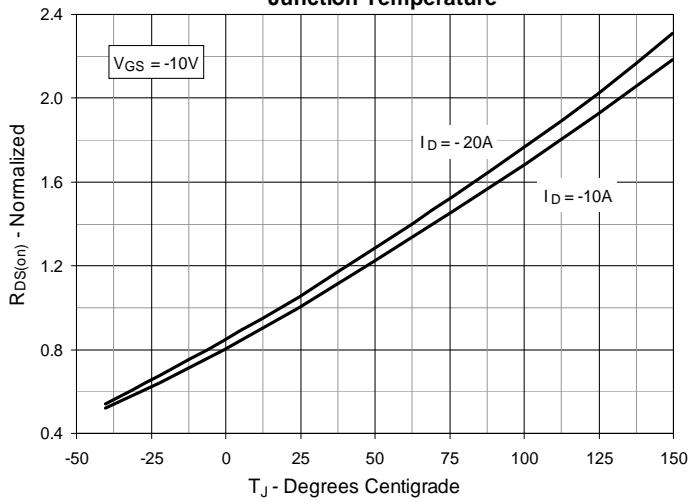
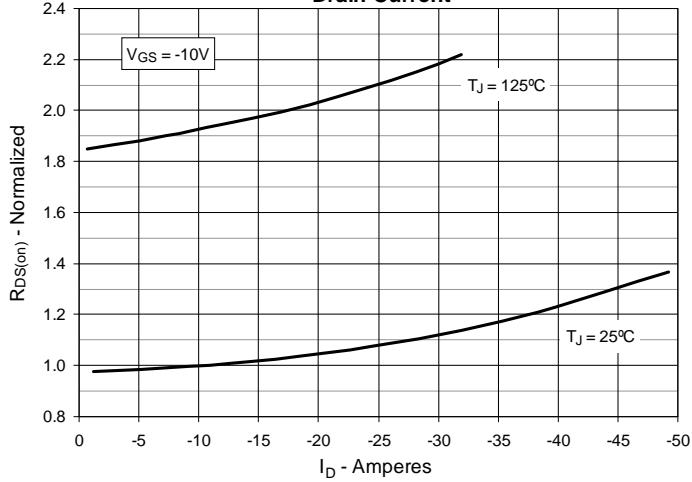
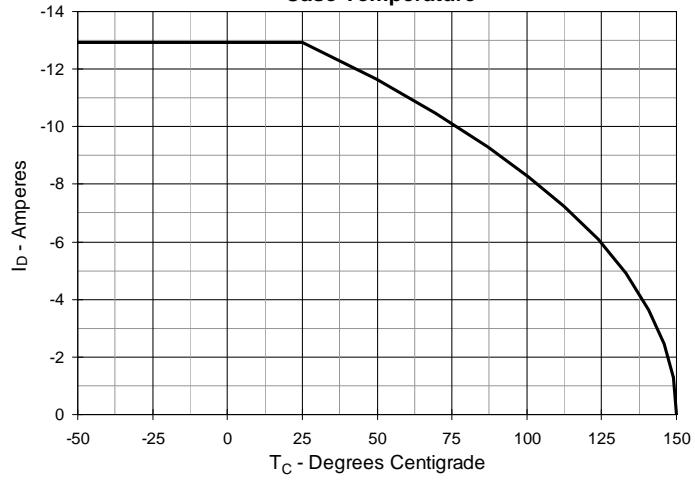
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ **Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$** **Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$** **Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -10\text{A}$ Value vs. Junction Temperature****Fig. 5. $R_{DS(on)}$ Normalized to $I_D = -10\text{A}$ Value vs. Drain Current****Fig. 6. Maximum Drain Current vs. Case Temperature**

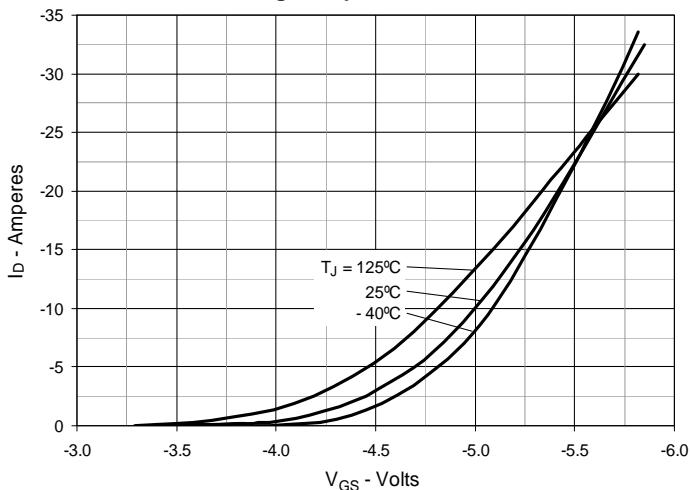
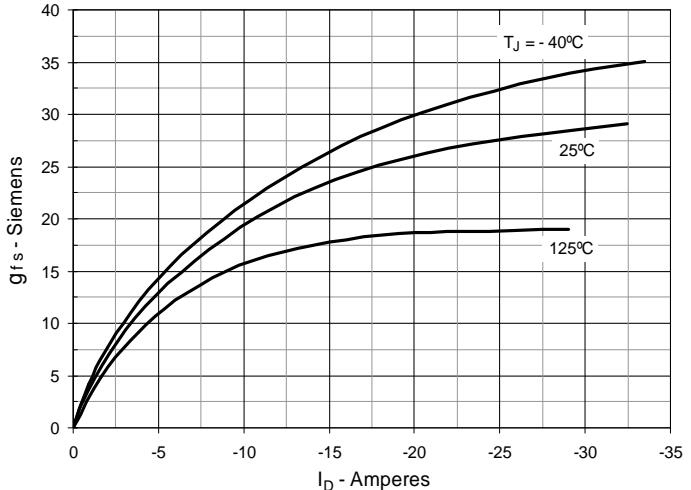
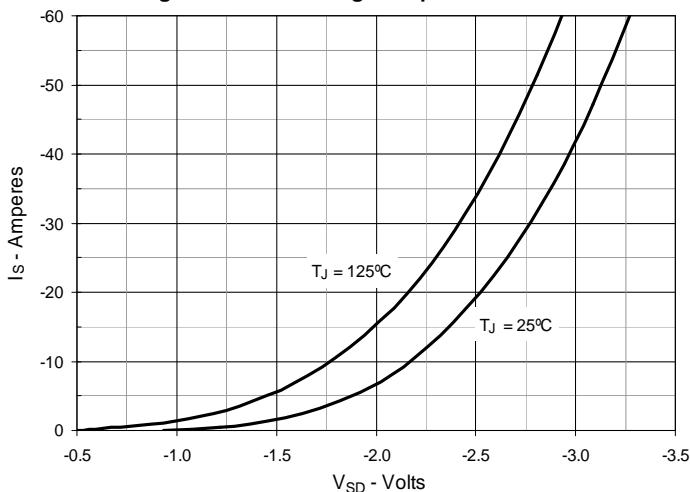
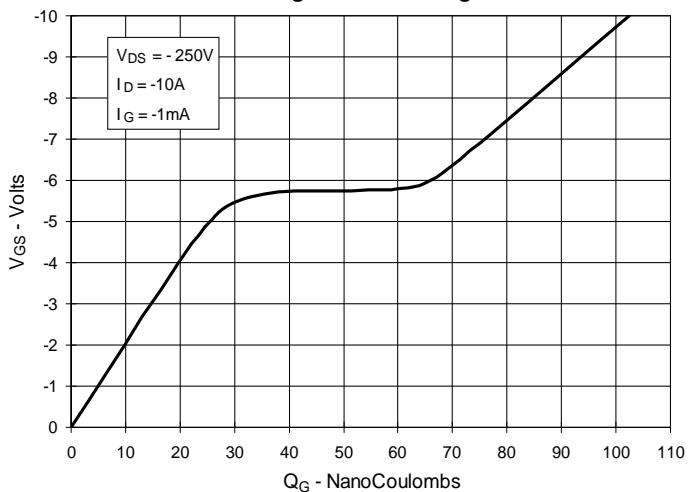
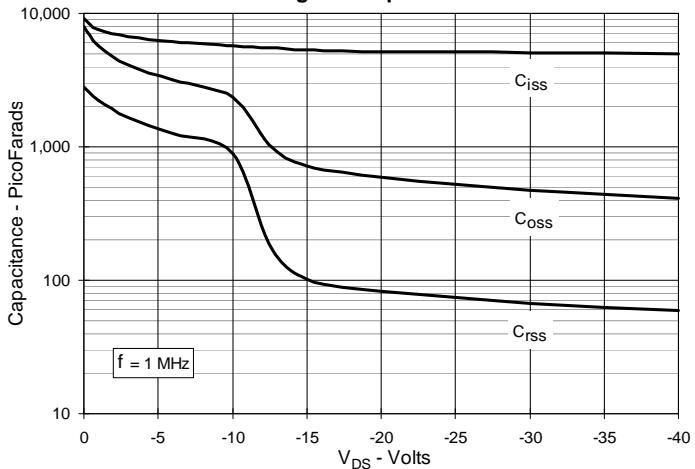
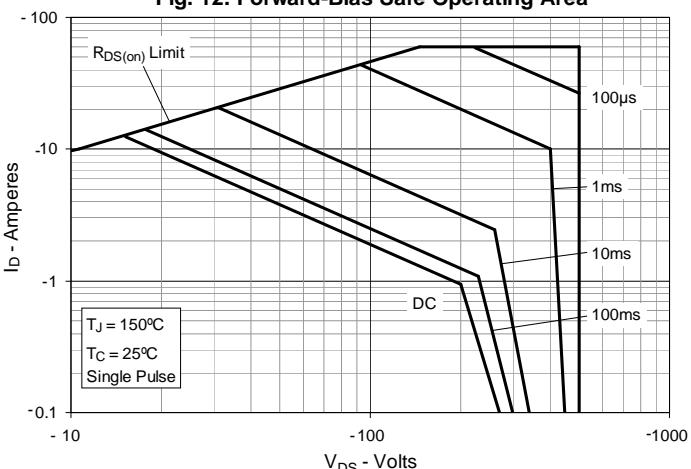
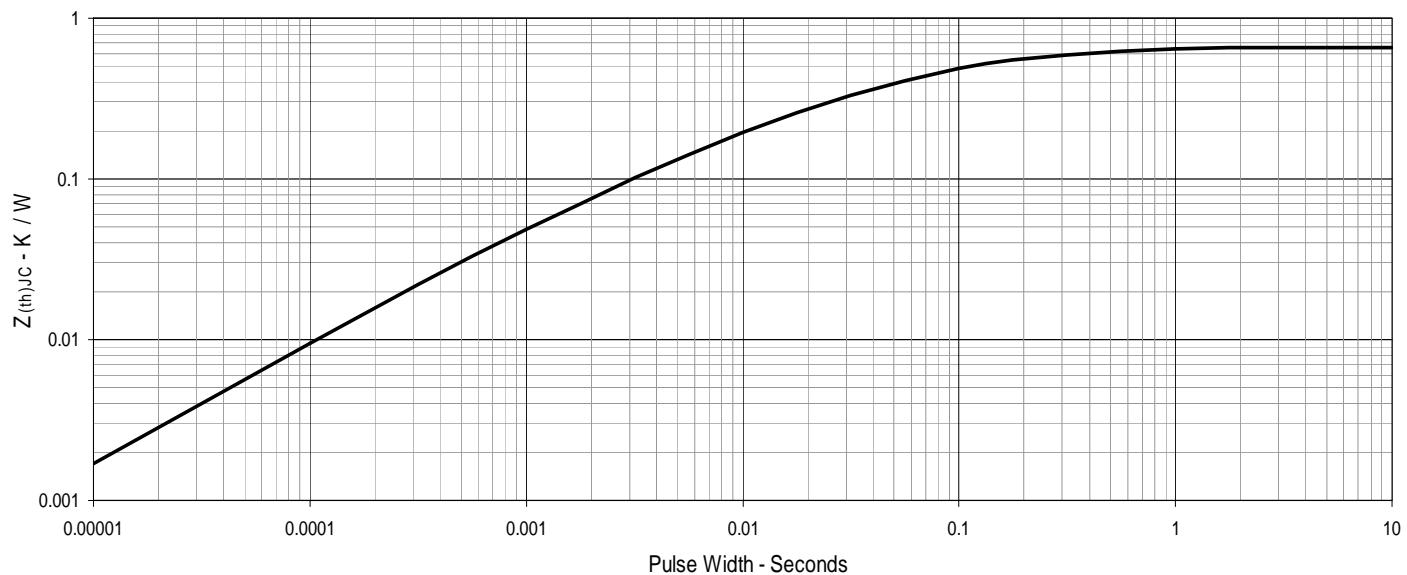
Fig. 7. Input Admittance**Fig. 8. Transconductance****Fig. 9. Forward Voltage Drop of Intrinsic Diode****Fig. 10. Gate Charge****Fig. 11. Capacitance****Fig. 12. Forward-Bias Safe Operating Area**

Fig. 13. Maximum Transient Thermal Impedance

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